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Kind regards,

Team Nexperia

BUK9M52-40E

N-channel 40 V, 52 mΩ logic level MOSFET in LFPAK33

19 September 2016 Product data sheet

1. General description

Logic level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with $V_{GS(th)}$ rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

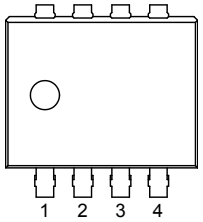
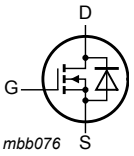
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T_j ≤ 175 °C		-	-	40	V
I_D	drain current	V_{GS} = 5 V; T_{mb} = 25 °C; Fig. 2		-	-	17.6	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 1		-	-	31	W
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 5 V; I_D = 5 A; T_j = 25 °C; Fig. 11		-	40.7	52	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	I_D = 5 A; V_{DS} = 32 V; V_{GS} = 5 V; T_j = 25 °C; Fig. 13; Fig. 14		-	2	-	nC

Scan or click this QR code to view the latest information for this product

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	Source	 LFPAK33 (SOT1210)	
2	S	Source		
3	S	Source		
4	G	Gate		
mb	D	Mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9M52-40E	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 8 leads	SOT1210

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9M52-40E	95240E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T_j ≤ 175 °C		-	40	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 kΩ		-	40	V
V_{GS}	gate-source voltage	DC; T_j ≤ 175 °C		-10	10	V
		Pulsed; T_j ≤ 175 °C	[1][2]	-15	15	V
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 1		-	31	W
I_D	drain current	V_{GS} = 5 V; T_{mb} = 25 °C; Fig. 2		-	17.6	A
		V_{GS} = 5 V; T_{mb} = 100 °C; Fig. 2		-	12.4	A
I_{DM}	peak drain current	pulsed; t_p ≤ 10 µs; T_{mb} = 25 °C; Fig. 3		-	70	A

Symbol	Parameter	Conditions		Min	Max	Unit
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
Source-drain diode						
I_S	source current	T_{mb} = 25 °C		-	17.6	A
I_{SM}	peak source current	pulsed; $t_p \leq 10$ µs; T_{mb} = 25 °C		-	70	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 17.6 A; $V_{sup} \leq 40$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[3][4]	-	4.98	mJ

[1] Accumulated pulse duration up to 50 hours delivers zero defect ppm.
[2] Significantly longer life times are achieved by lowering T_j and or V_{GS}
[3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
[4] Refer to application note AN10273 for further information.

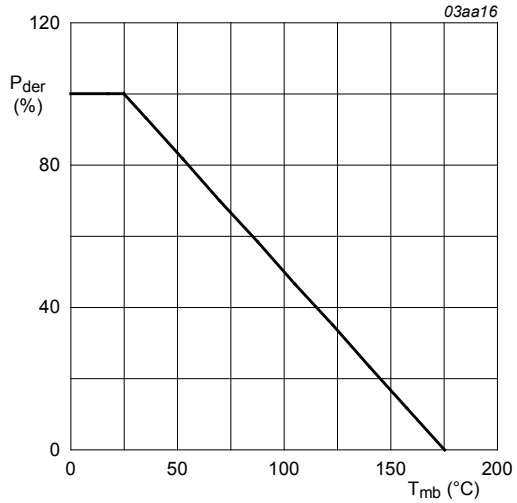
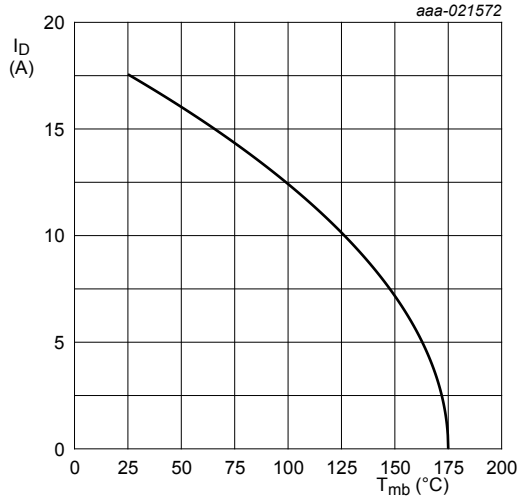


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

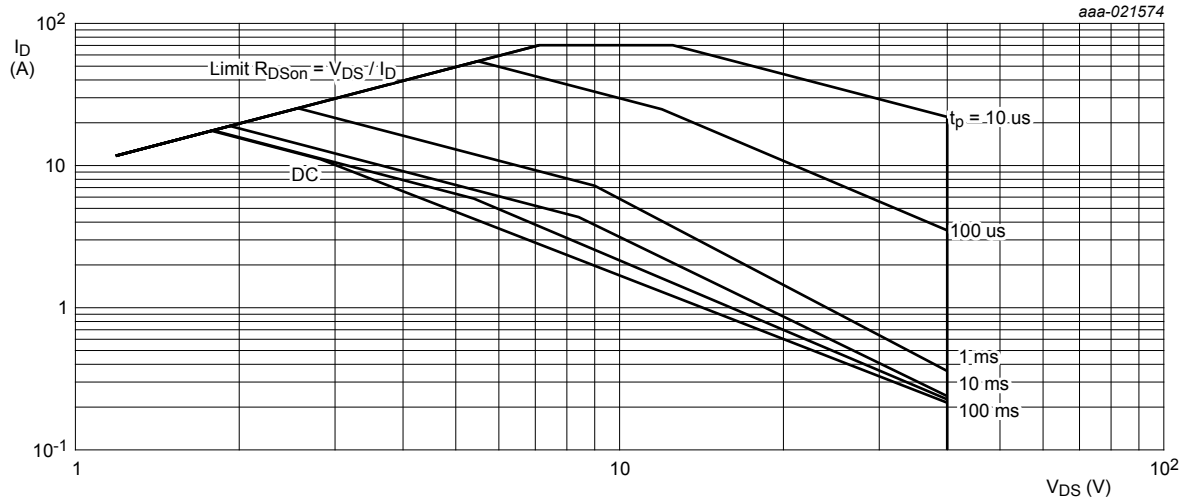
$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$



$V_{GS} \geq 5$ V

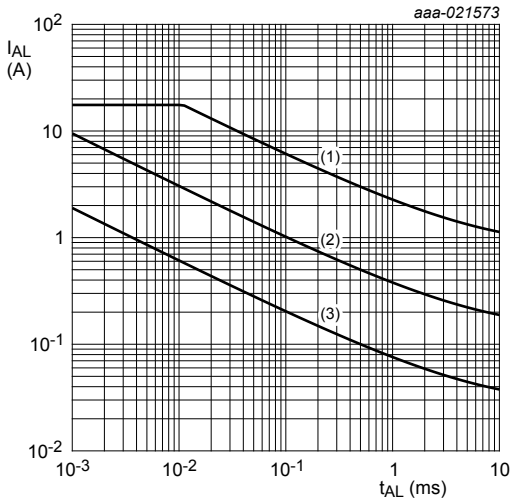
Fig. 2. Continuous drain current as a function of mounting base temperature

$$I_D = 17.6A \times \sqrt{\frac{175°C - T_{mb}}{150°C}} \quad \text{for } T_{mb} \geq 25°C$$



T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1) $T_{j\ (init)}$ = 25 °C; (2) $T_{j\ (init)}$ = 150 °C; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	4.27	4.8	K/W

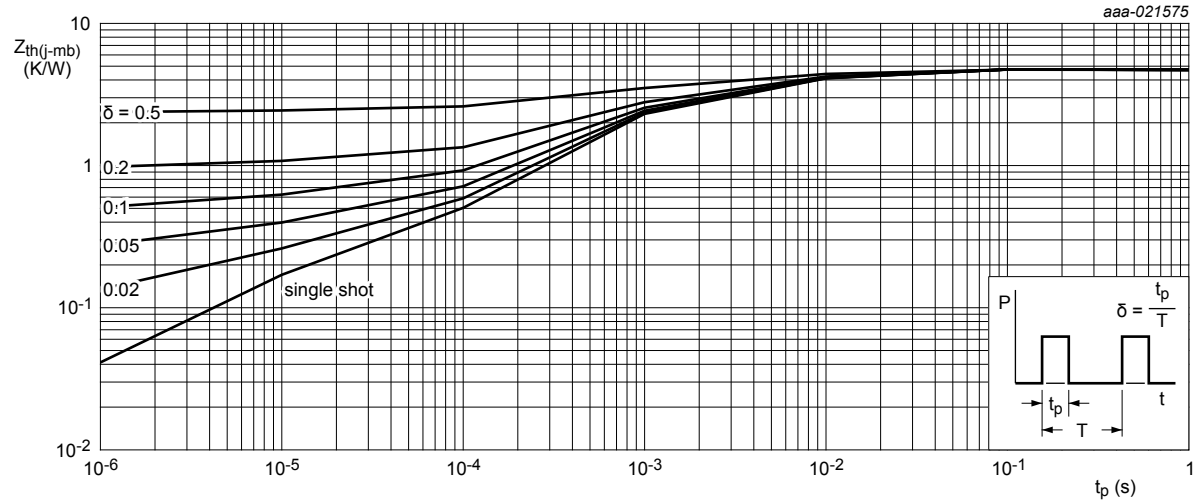


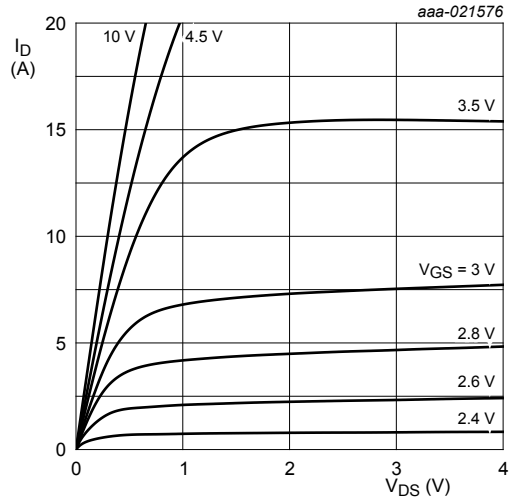
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

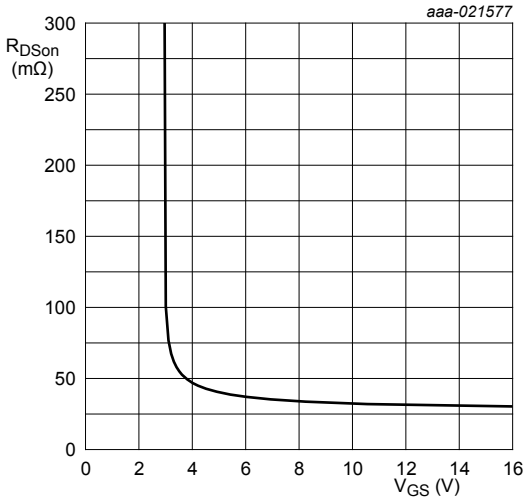
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		40	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; Fig. 9; Fig. 10		1.4	1.7	2.1	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; Fig. 10		-	-	2.45	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; Fig. 10		0.5	-	-	V
I_{DSS}	drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C		-	0.01	1	µA
		V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175 °C		-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 5 V; I_D = 5 A; T_j = 25 °C; Fig. 11		-	40.7	52	mΩ
		V_{GS} = 10 V; I_D = 5 A; T_j = 25 °C; Fig. 11		-	32.4	40	mΩ
		V_{GS} = 5 V; I_D = 5 A; T_j = 175 °C; Fig. 12		-	-	101	mΩ
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 5 A; V_{DS} = 32 V; V_{GS} = 5 V; T_j = 25 °C; Fig. 13; Fig. 14		-	4.5	-	nC
Q_{GS}	gate-source charge			-	1.1	-	nC
Q_{GD}	gate-drain charge			-	2	-	nC

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
C_{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; Fig. 15		-	306	407	pF
C_{oss}	output capacitance			-	59	70	pF
C_{rss}	reverse transfer capacitance			-	41	56	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 30 V; R_L = 5 Ω; V_{GS} = 5 V; $R_{G(ext)}$ = 5 Ω; T_j = 25 °C		-	5.3	-	ns
t_r	rise time			-	6.7	-	ns
$t_{d(off)}$	turn-off delay time			-	8.1	-	ns
t_f	fall time			-	5	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 5 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 16		-	0.85	1.2	V
t_{rr}	reverse recovery time	I_S = 5 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 25 V; T_j = 25 °C		-	10.9	-	ns
Q_r	recovered charge			-	4.9	-	nC



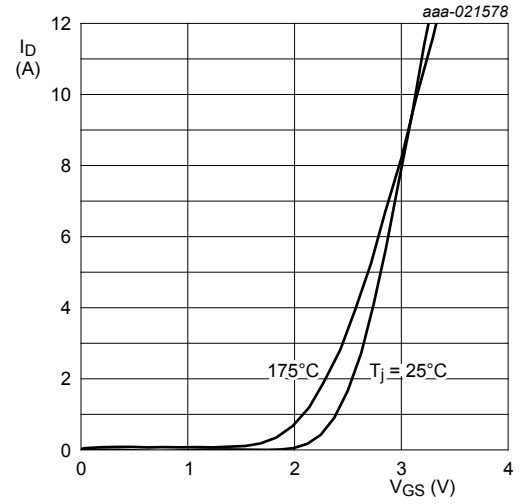
T_j = 25 °C

Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values



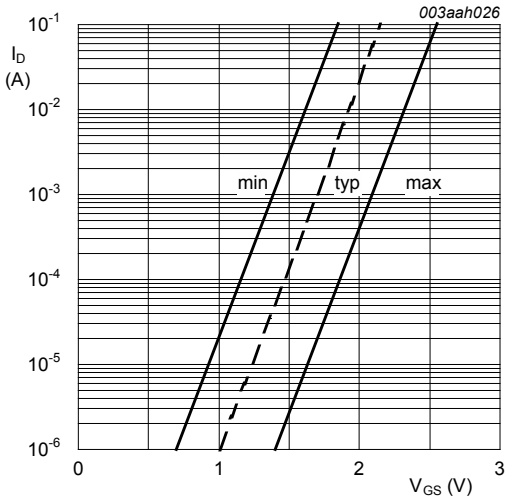
T_j = 25 °C; I_D = 5 A

Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



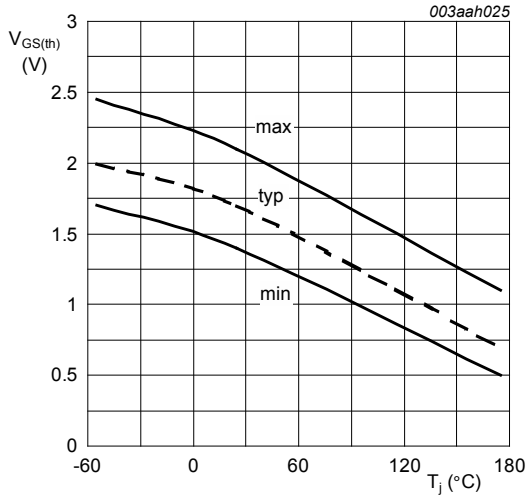
V_{DS} = 12 V

Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



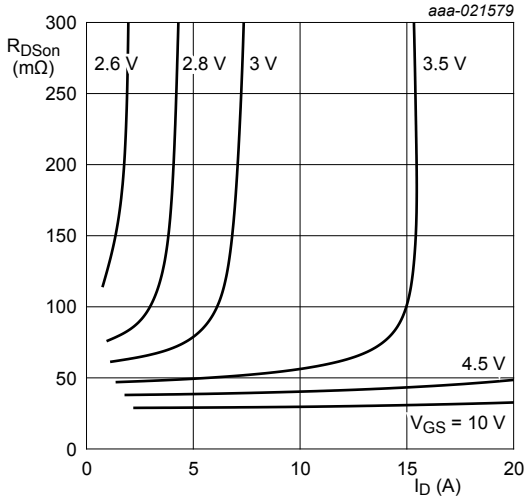
T_j = 25 °C; V_{DS} = 5 V

Fig. 9. Sub-threshold drain current as a function of gate-source voltage



I_D = 1mA; V_{DS} = V_{GS}

Fig. 10. Gate-source threshold voltage as a function of junction temperature



T_j = 25 °C

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

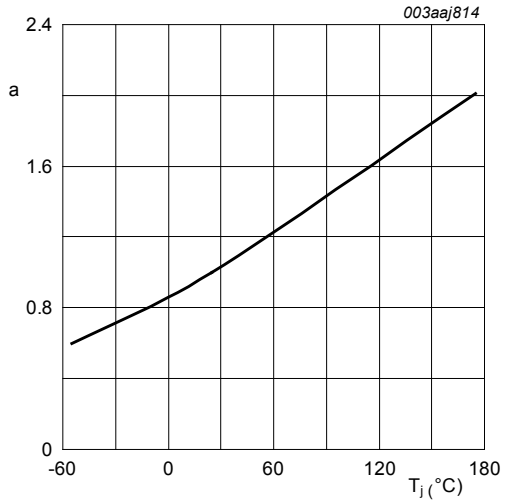
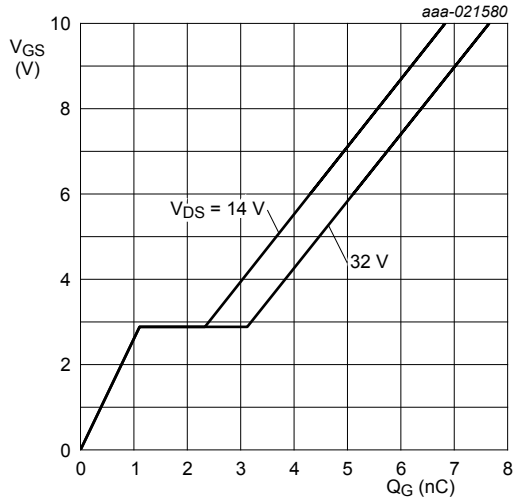


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$



T_j = 25 °C; I_D = 5 A

Fig. 13. Gate-source voltage as a function of gate charge; typical values

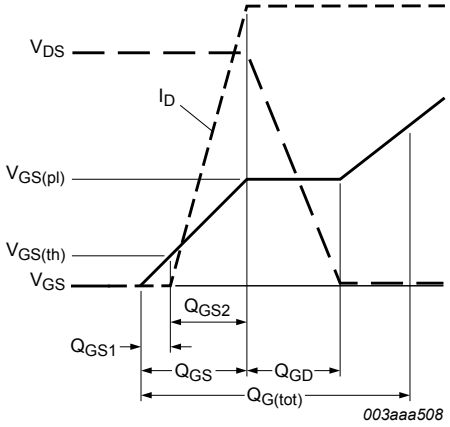
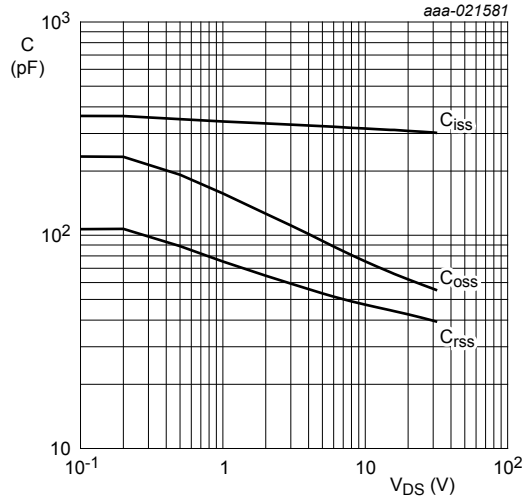
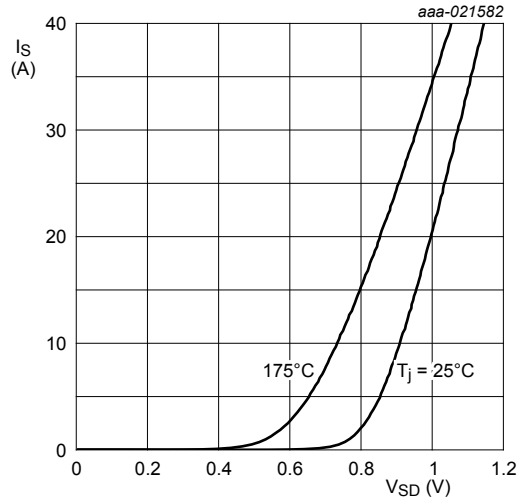


Fig. 14. Gate charge waveform definitions



V_{GS} = 0 V; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



V_{GS} = 0 V

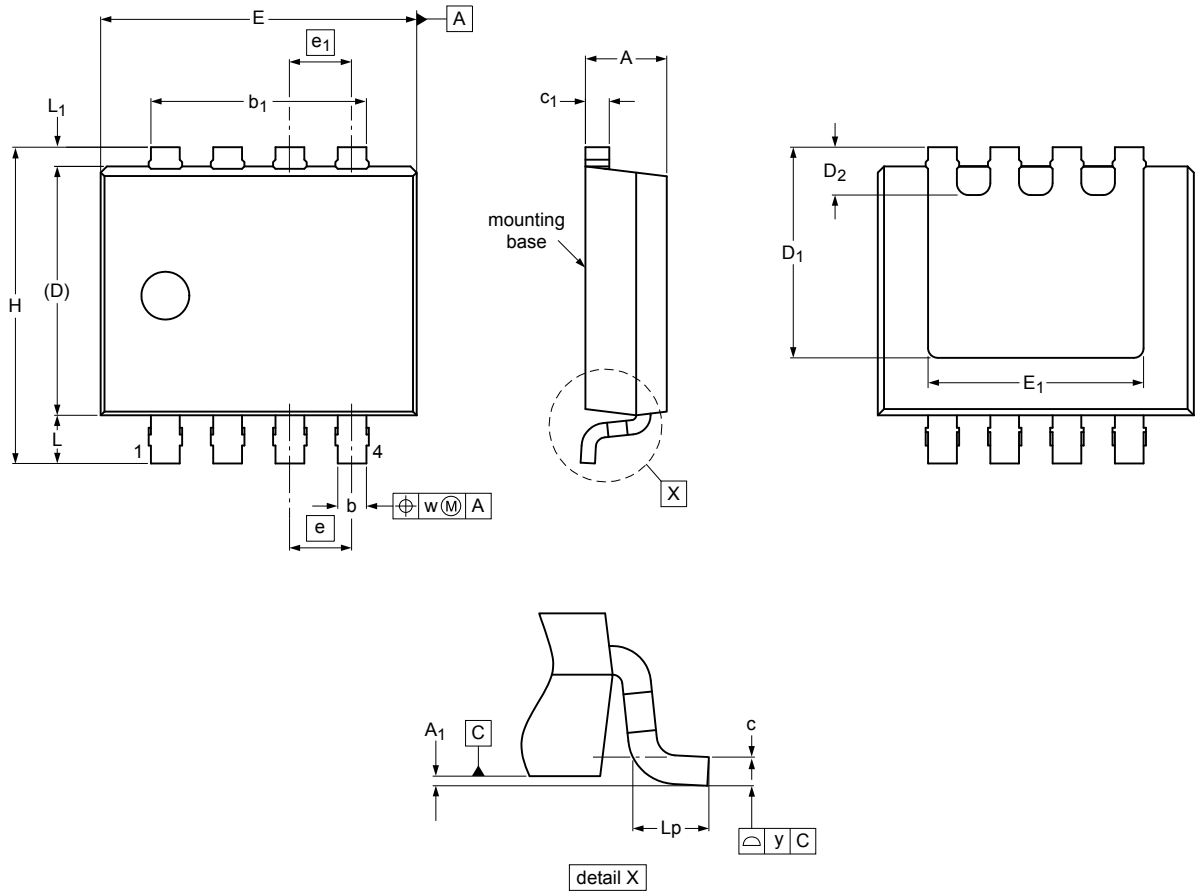
Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

11. Application information

For guidance on how to use and understand this datasheet, please refer to application note AN11158 "Understanding power MOSFET datasheet parameters".

12. Package outline

Plastic single ended surface mounted package (LFPAK33); 8 leads **SOT1210**



Dimensions

Unit(1)		A	A_1	b(1)	b_1(1)	c	c_1	D ref	D_1	D_2	E(1)	E_1	e	e_1	H	L	L_1	L_p	w	y
mm	max	0.90	0.10	0.35	2.4	0.20	0.30		2.35		3.40	2.45			3.40	0.65	0.25	0.50		
	nom							2.60		0.50			0.65	0.65					0.20	0.10
	min	0.80	0.00	0.25	2.2	0.10	0.20		1.90		3.20	2.00			3.20	0.45	0.13	0.30		

Note
1. Plastic or metal protrusions of 0.15 mm per side are not included.

sot1210_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1210						~~14-04-25~~ 16-08-09

Fig. 17. Package outline LFPAK33 (SOT1210)

13. Legal information

13.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Date of release: 19 September 2016